**Power LDMOS transistor** 

Rev. 1 — 12 November 2010

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

150 W LDMOS power transistor for base station applications at frequencies from 2500 MHz to 2700 MHz.

#### Table 1. Typical performance

Typical RF performance at  $T_{case} = 25 \ ^{\circ}C$  in a common source class-AB production test circuit.

Mode of operation	f	I <sub>Dq</sub>	$\mathbf{V}_{\text{DS}}$	P <sub>L(AV)</sub>	Gp	$\eta_{\textbf{D}}$	ACPR <sub>885k</sub>	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)	(dBc)
IS-95	2500 to 2700	1200	28	30	16.5	26	-47 <mark>[1]</mark>	-
Single carrier W-CDMA	2500 to 2700	1200	28	45	16.5	31	-	-38 <mark>[2]</mark>

[1] Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

[2] 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R<sub>th</sub> providing excellent thermal stability
- Designed for broadband operation (2500 MHz to 2700 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### **1.3 Applications**

 RF power amplifiers for base stations and multi carrier applications in the 2500 MHz to 2700 MHz frequency range



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2 sym117

## 2. Pinning information

Pin	Description		Simplified outline	Graphic symbol
BLF7G27	7L-150P (SOT539A)			
1	drain1			
2	drain2			1 .L
3	gate1		5	
4	gate2		3 4	
5	source	<u>[1]</u>		4 <b>1</b> 2 sym117
BLF7G27	7LS-150P (SOT539B)			
1	drain1			
2	drain2			
3	gate1		5	

[1]

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4

[1] Connected to flange.

### 3. Ordering information

4

5

#### Table 3.Ordering information

gate2

source

Type number	Package					
	Name	Description	Version			
BLF7G27L-150P	-	flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLF7G27LS-150P	-	earless flanged balanced LDMOST ceramic package; 4 leads	SOT539B			

## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage		-	65	V
V <sub>GS</sub>	gate-source voltage		-0.5	+13	V
I <sub>D</sub>	drain current		-	37	А
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

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### 5. Thermal characteristics

1	Table 5.	Thermal characteristics			
	Symbol	Parameter	Conditions	Тур	Unit
	R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case} = 80 \ ^{\circ}C; P_{L} = 30 \ W$	0.25	K/W

### 6. Characteristics

Table 6. C	haracteristics
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 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

<b>Typ</b> - 1.9	Max - 2.3	Unit V
1.9	2.3	17
		V
-	5	μA
5 19	-	A
-	500	nA
0.86	-	S
0.14	-	Ω
	5 19 - 0.86	5 19 - - 500 0.86 -

## 7. Test information

Remark: All testing performed in a class-AB production test circuit.

#### Table 7. Functional test information

Mode of operation: 1-carrier N-CDMA, single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF, channel bandwidth is 1.2288 MHz;  $f_1 = 2500$  MHz;  $f_2 = 2700$  MHz; RF performance at  $V_{DS} = 28$  V;  $I_{Dq} = 1200$  mA;  $T_{case} = 25$  °C; unless otherwise specified.

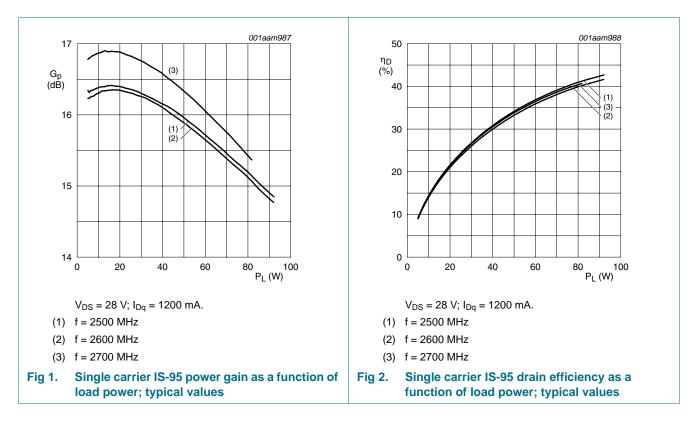
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P <sub>L(AV)</sub>	average output power		-	30	-	W
G <sub>p</sub>	power gain		14.8	16.5	-	dB
RL <sub>in</sub>	input return loss		-	-10	-	dB
$\eta_{D}$	drain efficiency		22	26	-	%
ACPR <sub>885k</sub>	adjacent channel power ratio (885 kHz)		-43	-47	-	dBc

### 7.1 Ruggedness in class-AB operation

The BLF7G27L-150P and BLF7G27LS-150P are capable of withstanding a load mismatch corresponding to VSWR = 20 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 1200 mA;  $P_L$  = 35 W (IS-95); f = 2500 MHz.

### 7.2 Single carrier IS-95

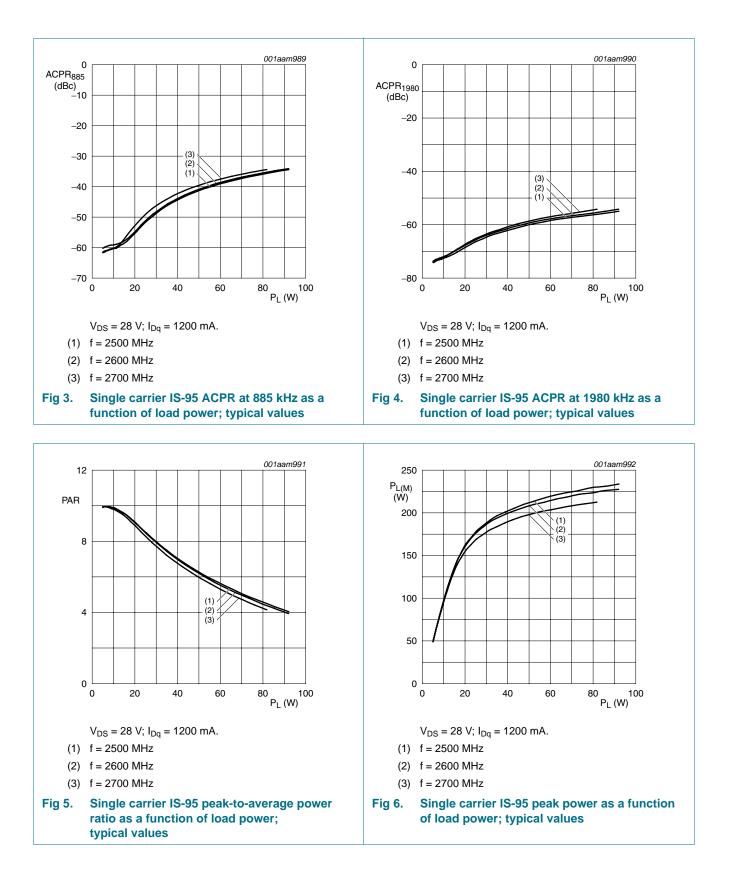
Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.



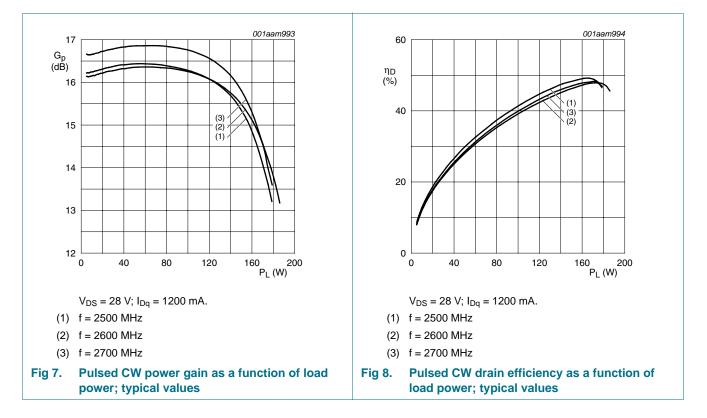
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# BLF7G27L-150P; BLF7G27LS-150P

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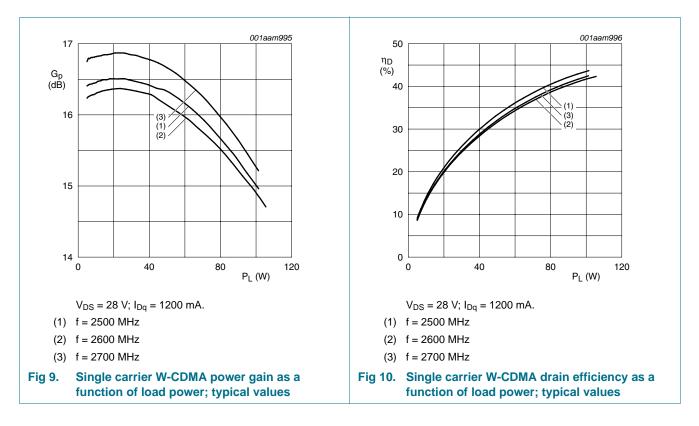


#### 7.3 Pulsed CW

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### 7.4 Single carrier W-CDMA

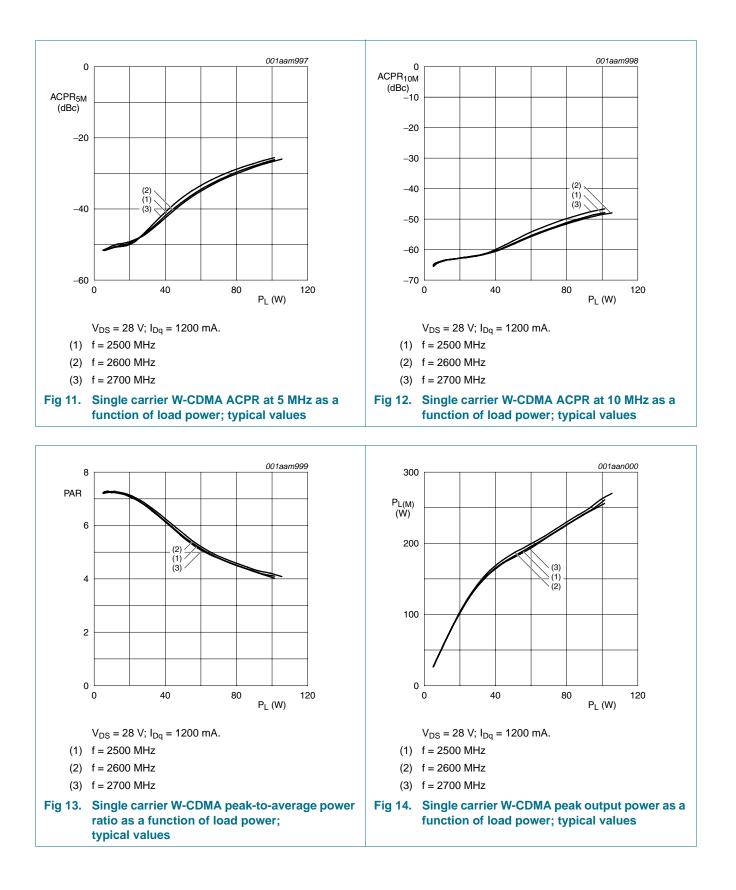
3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.



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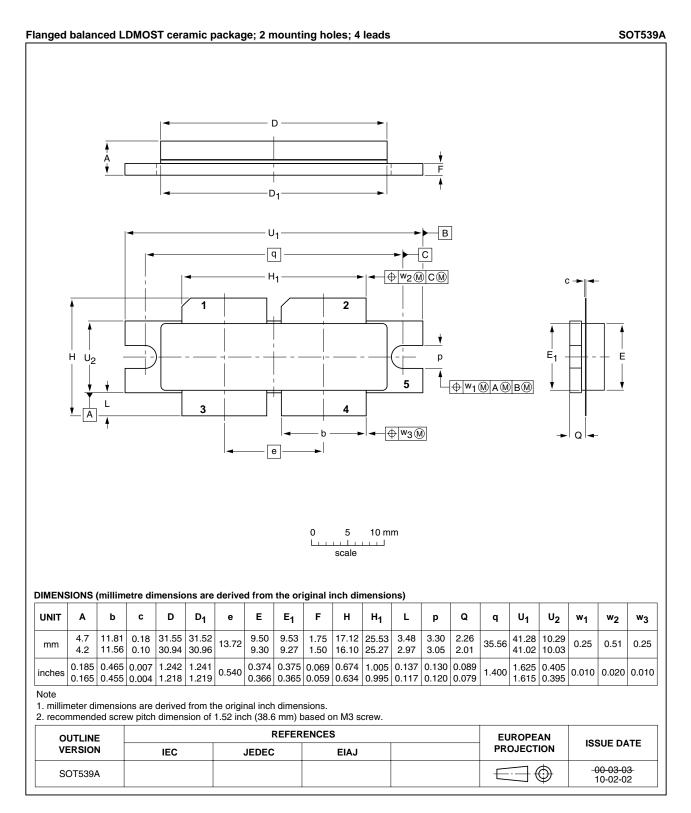
# BLF7G27L-150P; BLF7G27LS-150P

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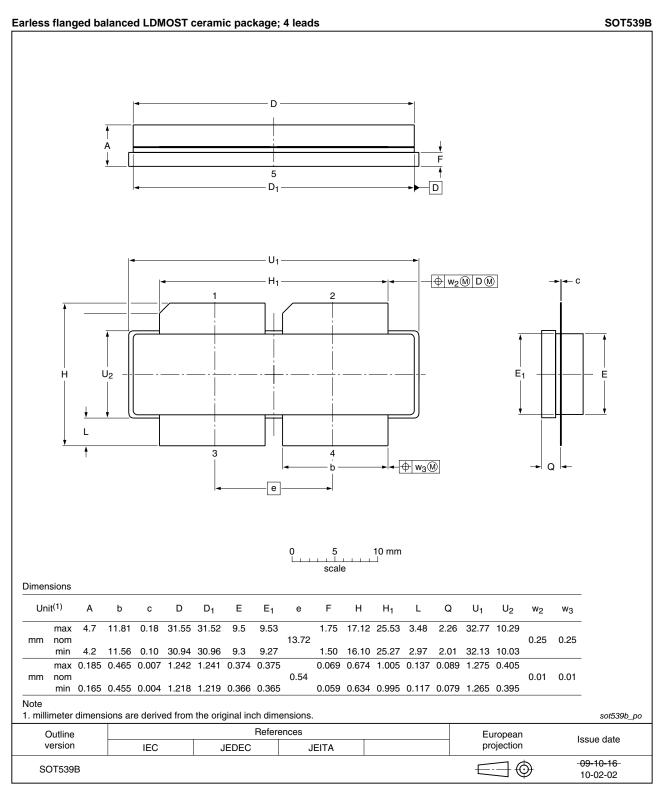
### 8. Package outline



#### Fig 15. Package outline SOT539A

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#### Fig 16. Package outline SOT539B

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## 9. Abbreviations

Table 8.	Abbreviations
Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
IS-95	Interim Standard 95
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
N-CDMA	Narrowband Code Division Multiple Access
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## **10. Revision history**

Table 9.         Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G27L-150P_7G27LS-150P v.1	20101112	Product data sheet	-	-

## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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